





GLADYSHEVSKIY, Ye.I.; LAKH, V.I.; SKOLOZDRA, R.V.; STADNYK, B.I.

Investigating the mutual solubility of group IV, V, and VI transition metal silicides. Porosh.met. 4 no.4:15-20 JI-Ag '64. (MIRA 18:8)

1. L'vovskiy gosudarstvennyy universitet imeni Franko.

STADNYI, B.I.; SAMSONOV, G.V.

Use of thermocouples in high-temperature measurements.

Teplofiz. vys. temp. 2 no.4:634-647 J1-Ag '64.

(MIRA 17:9)

1. Konstruktsionnoye byuro "Termopribor" i Institut problem  
materialovedeniya AN SSSR.























STADNYUK, Z.Ya.

Use of polyester varnishes in the manufacture of furniture.  
Bum. i der. prom. no.3:3-6 J1-S '64.

(MIRA 17:11)





STADUKHIN, D.G., dotsent

Economic efficiency of basic capital assets of mining enterprises.  
Izv.vys.ucheb.zav.; gor.zhur. no.3:65-72 '61. (MIRA 15:4)

1. Sverdlovskiy gornyy institut imeni V.V.Vakhrusheva; rekomendovana  
kafedroy politicheskoy ekonomii Sverdlovskogo gornogo instituta.  
(Sverdlovsk Province--Mining industry and finance)







STADUKHIN, V.D.

Determination of the magnetic susceptibility of rocks and ores by measuring the intensity of the magnetic field in holes with artificial magnetization in order to detect and evaluate iron ore deposits.  
Izv. AN SSSR. Ser. geofiz. no.9:1381-1385 S '63. (MIRA 16:10)

1. Institut geofiziki Ural'skogo filiala AN SSSR.

IVANOV, N.A.; STADUKHTN, V.D.; ULITINA, G.G.

Charts for the approximate calculation of anomalous effect in the  
methods of magnetic profiling and sounding. Trudy Inst.geofiz.UFAN  
SSSR no.3:65-71 '65. (MIRA 18:8)

STADUKHIN, V.D.; ULITINA, G.G.

Magnetic profiling with square and rectangular frames in the  
Techenskoye iron ore deposit. Trudy Inst.geofiz.UFAN SSSR (MIRA 18:8)  
no.3:73-77 '65.

ALEKNIKOV, A.L.; STADUKHIN, V.D.; ULITINA, G.G.

Interpretation of magnetic and gravity measurements using data of  
artificial magnetic biasing. Trudy Inst.geofiz.UFAN SSSR no.3:97-  
102 '65. (MIRA 18:8)

STAER, Jan, mgr inz.

An example of correction of the power coefficient in the plant  
and resulting advantages. Energetyka przem 10 no.12:427-429  
D '62.

1. PR-2 Elektromontaz, Katowice.





SRM 3.1.

"Haliemia in Ischaemic Hypothermia. p. 213, (SLEB, Vol. 6, No. 210, 1953, Belograd, Yugoslavia)

SO: Monthly List of East European Accessions, (SEAL), LO, Vol. 4, No. 4, Apr 1959, Uncl.

RAMAN, M. [Ramans, M.]; STAFETSKIY, L. [Stafeckis, L.]

Results of testing the air conditioning system for passenger cars.  
Izv. AN Latv. SSR no.5:53-60 '62. (MIRA 16:7)

1. Institut energetiki AN Latviyskoy SSR.  
(Railroads--Cars--Air conditioning)









L 46166-66

ACC NR: AP6021537

lag. Orig. art. has: 13 formulas and 3 figures.

SUB CODE: 09,13/ SUBM DATE: 05May65/ ORIG REF: 004/ OTH REF: 002

Card 2/2

STAFYEV, A.

Miners in the broken work week (Sunday off). Sots.trud. no.11:94-  
95 N '56. (MLRA 10:1)

1. Nachal'nik OOT Gornogo upravleniya Kuznetskogo metallurgicheskogo  
kombinata.  
(Iron mines and mining) (Weekly rest-day)

STEFANOV, A.

The broken work wee (Sunday off) at mines has justified itself.  
Sots.trud no.9:106-108 S '57. (MLRA 10:9)

1. Nachal'nik otдела organizatsii truda Gornogo upravleniya  
Kuznetskogo metallurgicheskogo kombinata.  
(Kuznetsk Basin--Iron mines and mining)





STAFEYEV, A.

Comprehensive organization of work in the mines of the  
Kuznetsk Metallurgical Combine. Sots. trud 6 no.6:121-123  
Je '61. (MIRA 16:8)

1. Nachal'nik otдела ekonomicheskikh issledovaniy  
Vostochnogo nauchno-issledovatel'skogo gornorudnogo instituta,  
Stalinsk.

BOGOMOLOV, M.; STAFYEV, A.

Determining the number of repair-shop workers in shifting  
to a centralized repair system in an ore dressing and sintering  
plant. Biul.nauch. inform.: trud i zar. plata 5 no.3:41-44  
'62. (MIRA 15:3)

(Abagur--Ore dressing) (Abagur--Sintering)







STAFEEYEV, K.G.

Thrust in the Tungir trough (northeastern Transbaikalia). Geotektonika  
no.4:108-109 JI-Ag '65. (MIRA 18:8)

1. Vsesoyuznyy nauchno-issledovatel'skiy institut mineral'nogo  
syr'ya, Moskva.





STAFEEV, V.I.

4553. OPERATION OF A CRYSTAL AMPLIFIER WITH  
(MINORITY CARRIER) DEPLETION. V.I. Stafeev,

V.M. Tuchkevich and N.S. Yakovchuk.  
Zh. tekhn. Fiz., Vol. 26, No. 1, 15-21 (1956). In Russian.

The operation of crystal triodes with negative emitter bias is described. The resulting depletion of minority carriers in the base region enables amplification to be obtained at higher temperatures and frequencies than with positive emitter bias. The new mode of operation would probably be still more advantageous in these respects with triodes designed for it. No discontinuity in characteristics is found on going from positive to negative bias, and a mixed mode of operation is possible.

C.H.L. Goodman









Note on Current Multiplication of Minority Carriers in the 57-lo-2/33  
Non-Ideal p-n Junction.

ASSOCIATION. Leningrad Physical-Technical Institute AN USSR (Leningradskiy  
fiziko-tekhnicheskiy institut AN SSSR).

SUBMITTED. April 20, 1957.

AVAILABLE. Library of Congress.

Card 3/3

SEAFYEV, V.I., Cand Phys-Math Sci — (disc) "New principles of action  
of semiconductor <sup>devices</sup> ~~apparatus~~." Len, 1958. 10 pp (Acad Sci USSR. Phys  
Tech ~~Inst~~ Inst), 150 copies (KL, 44-52, 119)

-6-







Influence of Resistance of the Semiconductor Body      SOV/57-58-8-2/37  
Upon the Shape of the Diode Voltage Versus Current Curves

and 9 references, 4 of which are Soviet.

ASSOCIATION: Leningradskiy fiziko-tekhnicheskii institut, AN SSSR (Leningrad  
Physical and Technical Institute, AS USSR)

SUBMITTED: April 10, 1958

Card 4/4







LOKTIONOV, A.A.; STAFYEV, V.I.; TAKIBAYEV, Zh.S.

Studying the spatial distribution of nuclear disintegrations with  
thick nuclear emulsions. Vest.AN Kazakh.SSR 14 no.10:49-59 0 '58.  
(MIRA 11:12)

(Cosmic rays) (Photography, Particle track)

STAFYEV, V.I.

Modulation of the diffusion displacement length as a new principle  
in the operation of semiconducting devices. Fiz. tver. tela 1 no.6:  
841-847 Je '59. (MIRA 12:10)

1. Leningradskiy fiziko-tekhnicheskoy institut AN SSSR.  
(Germanium diodes)

STAFEEYEV, V. I.

Current - voltage characteristics of a diode during superhigh levels  
of injection. Fiz. tver. tela 1 no.6:848-850 Je '59.  
(MIRA 12:10)

1. Leningradskiy fiziko-tekhnicheskoy institut AN SSSR.  
(Diodes)











STAFEYEV, V. I., Doc: PHYS-MATH SCI, "NEW ~~GENERATION~~  
*(the action of)*  
PRINCIPLES OF SEMICONDUCTOR DEVICES." MOSCOW, 1961.  
(ACAD SCI USSR, PHYS INST IM P. N. LEBEDEV). (KL, 3-61,  
202).

STAFEYEV, V.I.

Direct branch of volt-ampere characteristic of a nonsymmetric diode. Fiz. tver. tela 3 no.1:185-193 Ja '61. (MIRA 14:3)

1. Leningradskiy fiziko-tekhnicheskii institut AN SSSR imeni akad. A.F. Ioffe.

(Diodes)



























STAFYEV, V.I.; VAN SHOU-TSZUYE [Wang Shou-chüeh]; FILINA, L.V.

Transistors with N-shaped characteristics. Radiotekh. i elektron.  
7 no.8:1404-1408 Ag '62. (MIRA 15:8)

1. Fiziko-tekhnicheskii institut im. A.F.Ioffe AN SSSR.  
(Transistors)















STAFYEV, V.I.

Some properties of germanium with admixture of gold. Fiz. tver. tela  
5 no.11:3095-3104 N '63. (MIRA 16:12)

1. Fiziko-tekhnicheskiy institut imeni A.F.Ioffe AN SSSR, Leningrad.





STAFEEYEV Vitaliy Ivanovich, KALAKUSHAN, Emiliya Ivanovna.

[Magnetodiodes; semiconductor devices with high magnetic sensitivity] Magnitodiody, poluprovodnikovye pribory s vysokoi magnitochuvstvitel'nost'iu. Leningrad, Leningradskii dom nauchno-tekhnicheskoi propagandy, 1964. 33 p. (Poluprovodniki, no.13) (MIRA 17.4)

SONDAYEVSKIY, V.P.; STAFYEYEV, V.I.

Injectons into semiconductors with deep impurity levels. Fiz.  
tver. tela 6 no.1:80-91 Ja '64. (MIRA 17:2)

1. Fiziko-tekhnicheskiy institut imeni A.F.Ioffe AN SSSR, Lenin-  
grad.

ACCESSION NR: AP4040914

S/0109/64/009/006/1040/1046

AUTHOR: Shtager, A. P.; Stafeyev, V. I.

TITLE: N-shaped characteristic of the double-base diode

SOURCE: Radiotekhnika i elektronika, v. 9, no. 6, 1964, 1040-1046

TOPIC TAGS: semiconductor, semiconductor diode, double base diode, N shaped characteristic

ABSTRACT: Assuming that: (a) the model is single-dimensional, (b) the semiconductor has a near-intrinsic conductivity, (c) the emitter is of the point-contact type, and (d) the injection coefficient is 1, these formulas are developed to describe the current-voltage characteristic:

$$\text{base-to-base voltage } V_{bb} = \left[ V_e - \frac{kT}{q} \ln \left( \frac{I_e}{I_s} + 1 \right) \right] \left( \frac{R_n}{R_n + 1} \right) - I_e R_n$$

$$\text{base-to-base current } I_{bb} = \left[ V_e - \frac{kT}{q} \ln \left( \frac{I_e}{I_s} + 1 \right) - I_e R_n \right] / R_n$$

where  $V_e$  and  $I_e$  are the emitter voltage and current,  $I_s$  is the saturation current

Card 1/2

ACCESSION NR: AP4040914

$R_{11}$  is the resistance between the emitter and the principal base, and  $R_{12}$  is the resistance between the emitter and the second base. Double-base symmetrical and nonsymmetrical diodes described in the authors' earlier work (Rad. i elektronika, 1963, 8, 7, 1199) were tested; their p-n junction saturation current was about 20 microamp and  $I_s/L \approx 3$ . Due to the finite size of the emitter in the real diodes, the theoretical and experimental I/V N-shaped characteristics stand only qualitative comparison. The best base-to-base characteristics were observed in the nonsymmetrical diode connected with a short principal base. Optimum switching characteristics were obtained with minimum  $I_s$ , and  $L$  securing the required resistance of the closed diode;  $I_s$  is the principal base length,  $L$  is the diffusion length. Orig. art. has: 8 figures and 8 formulas.

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